

IN THE SPECIFICATION

Please amended the paragraph beginning on page 13, line 21 as follows:

Figure 3H shows the semiconductor structure following the next sequence of processing. Portions of the inhibiting layer 330, conductive layer 338, insulation layer ~~[[336]]~~ 326, and conductive layer 334 are exposed where the mask 354 does not cover. These exposed portions are selectively removed as well as the mask 354. Once these exposed portions are removed, semiconductor structures of interest, such as capacitors 336, are defined and remained abutting the insulation layer 320. These exposed portions may be removed by etching or by other suitable removal techniques known in the art. Removal techniques are generally dependent upon the material of construction of the layer to be removed as well as the surrounding layers to be retained.